

DECLARATION AND POWER OF ATTORNEY

As a below named inventor, I hereby declare that:

My residence, post office address and citizenship are as stated below next to my name.

I believe I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled: **A METHOD OF DEPOSITING TUNGSTEN NITRIDE USING A SOURCE GAS COMPRISING SILICON**; the specification of which is attached hereto.

I hereby state that I have reviewed and understand the contents of the above identified specification, including the claims.

I acknowledge the duty to disclose information which is material to patentability as defined in Title 37 of the Code of Federal Regulations, Section 1.56.

I hereby claim the benefit under Title 35 of the United States Code, Section 120 to which I am entitled and, insofar as the subject matter of each of the claims of this application is not disclosed in the prior United States application in the manner provided by the first paragraph of Title 35 of the United States Code, Section 112, I acknowledge the duty to disclose information which is material to patentability as defined in Title 37 of the Code of Federal Regulations, Section 1.56 which became available between the filing date of the prior application and the national or PCT international filing date of this application.

I hereby appoint the following attorney(s) and/or agent(s) to prosecute this application and to transact all business in the Patent and Trademark Office connected therewith:

William R. Bachand	Registration No. 34,980
Susan B. Collier	Registration No. 34,566
Angus C. Fox, III	Registration No. 31,828
Kevin D. Martin	Registration No. 37,882
Lia M. Pappas	Registration No. 34,095
David J. Paul	Registration No. 34,692

Send correspondence to: Susan B. Collier, Patent Agent
Micron Semiconductor, Inc.
Patent Department, MSS25
2805 East Columbia Road
Boise, Idaho 83706-9698

Direct phone calls to: Susan B. Collier
(208)368-4514

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Title 18 of the United States Code, Section 1001 and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

Inventor's Full Name: Scott Meikle

(First)

(MI)

Meikle

(Last)

Inventor's Signature: Scott Meikle

Date: Nov 23/94

Citizenship: Canada

Post Office Address: 1301 East Jefferson

Boise, Idaho 83712

City, State and
Country of Residence Boise, Idaho United States of America

Inventor's Full Name: Trung Doan

(First)

(MI)

Doan

(Last)

Inventor's Signature: Trung Doan

Date: 11/23/94

Citizenship: United States

Post Office Address: 1574 Shenandoah Drive

Boise, Idaho 83712

City, State and
Country of Residence Boise, Idaho United States of America

S/N 08/667,907**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE****PATENT**

Applicant: Scott G. Meikle et al.

Examiner: Thomas Bilodeau

Serial No.: 08/667,907

Group Art Unit: 1107

Filed: June 12, 1996

Docket: 303.444US2

Title: METHOD OF DEPOSITING TUNGSTEN NITRIDE USING A SOURCE GAS
COMPRISING SILICON**REVOCATION AND POWER OF ATTORNEY**

Assistant Commissioner for Patents
 Washington, D.C. 20231

In accordance with 37 C.F.R. Section 1.36, M.P.E.P. Section 402.05, 402.07, and 324
 please revoke any existing Powers of Attorney, if any, and appoint the following attorneys and/or
 patent agents to prosecute this application and to transact all business in the Patent and
 Trademark Office in connection therewith:

Anglin, J. Michael	Reg. No. 24,916	Hofmann, Rudolph P., Jr.	Reg. No. 38,187
Bianchi, Timothy E.	Reg. No. 39,610	Holloway, Sheryl S.	Reg. No. 37,850
Billig, Patrick G.	Reg. No. 38,080	Klima-Silberg, Catherine I.	Reg. No. 40,052
Billion, Richard E.	Reg. No. 32,836	Kluth, Daniel J.	Reg. No. 32,146
Brennan, Thomas F.	Reg. No. 35,075	Lemaire, Charles A.	Reg. No. 36,198
Brooks, Edward J., III	Reg. No. 40,925	Lundberg, Steven W.	Reg. No. 30,568
Clark, Barbara J.	Reg. No. 38,107	Lynch, Michael L.	Reg. No. 30,871
Drake, Eduardo E.	Reg. No. 40,594	Madrid, Andres N.	Reg. No. 40,710
Dryja, Michael A.	Reg. No. 39,662	Pappas, Lia M.	Reg. No. 34,095
Embreton, Janet E.	Reg. No. 39,665	Schwegman, Micheal L.	Reg. No. 25,816
Farney, W. Bryan	Reg. No. 32,651	Simboli, Paul B.	Reg. No. 38,616
Fogg, David N.	Reg. No. 35,138	Slifer, Russell D.	Reg. No. 39,838
Forrest, Bradley A.	Reg. No. 30,837	Viksnins, Ann S.	Reg. No. 37,748
Harris, Robert J.	Reg. No. 37,346	Woessner, Warren D.	Reg. No. 30,440

Serial Number: 08/667,907
Filing Date: June 12, 1996

TITLE: METHOD OF P

METHOD OF DEPOSITING TUNGSTEN NITRIDE USING A SOURCE GAS COMPRISING SILICON

Page 2
Dkt: 303.444US2

CERTIFICATE UNDER 37 CFR 53.73(b)

Micron Technology, Inc. hereby certifies that it is the assignee of the entire right, title and interest in the patent application identified above by virtue of an assignment from the inventor filed November 30, 1994 and recorded on Reel 7267, Frames 0790 - 0793. To the best of my knowledge and belief, title is in Micron Technology, Inc., the assignee.

Pursuant to 37 C.F.R. §3.73(b) I hereby declare that I, Michael L. Lynch, am empowered to sign this certificate on behalf of Micron Technology, Inc., the assignee.

I hereby declare that all statement made herein of my own knowledge are true, and that all statements made on information and belief are believed to be true.

Please direct all correspondence in this case to:

Schwegman, Lundberg, Woessner & Kluth, P.A.
P.O. Box 2938
Minneapolis, MN 55402
Telephone No. (612)373-6900

Date March 2007 By MLL
Michael L. Lynch
Title: Chief Patent Counsel
Micron Technology, Inc.